MICROWAVE POWER GaN HEMT

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

•BROAD BAND INTERNALLY MATCHED HEMT •HIGH POWER Pout= 51.0dBm at Pin= 43dBm

·HIGH GAIN

GL= 12.5dB at Pin= 20dBm

·LOW INTERMODULATION DISTORTION

IM3= -25dBc(Min.) at Pout= 44dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 40V IDSset= 0.8A f = 5.85 to 6.75GHz @Pin= 43dBm	dBm	50.0	51.0	_
Drain Current	IDS1		А	_	7.0	9.0
Power Added Efficiency	ηadd		%		38	
Linear Gain	GL	@Pin= 20dBm	dB	11.5	12.5	_
Gain flatness	ΔG		dB			±0.8
3rd Order Intermodulation Distortion	IM3	- Two-Tone Test Po= 44dBm, - (Single Carrier Level) Δf= 5MHz (IM3) Δf= 150MHz (IM3-2)	dBc	-25	-30	
	IM3-2		dBc	-25	-27	
Drain Current	IDS2		А			5.0
Channel Temperature Rise *1	∆Tch		°C		120	140

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 10 Ω

*1: Δ Tch = (VDS × IDS2 + Pin(two-tone) – Po(two-tone)) × Rth(c-c), calculated using parameters of IM3 test

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 30mA	V	-2.0	-3.0	-5.0
Gate-Source Breakdown Voltage	VGSO	IGS= -25mA	V	-10		_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	0.8	1.0

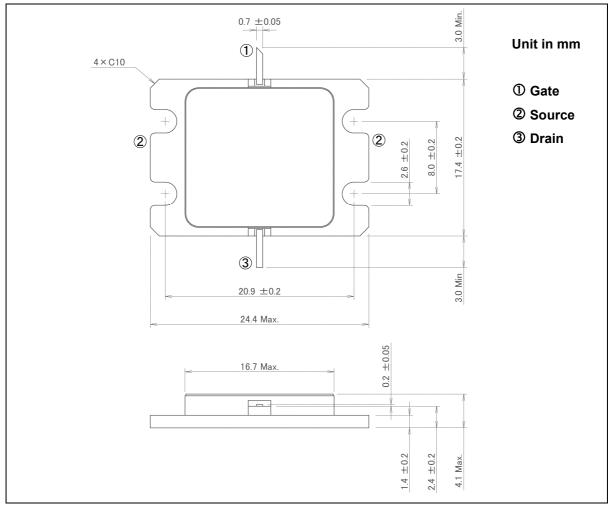
ELECTRICAL CHARACTERISTICS (Ta= 25°C)

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ABSOLUTE MAXIMUM RATINGS (Ta= 25° C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	A	12
Total Power Dissipation (Tc= 25°C)	PT	W	200
Channel Temperature	Tch	°C	225
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA06A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

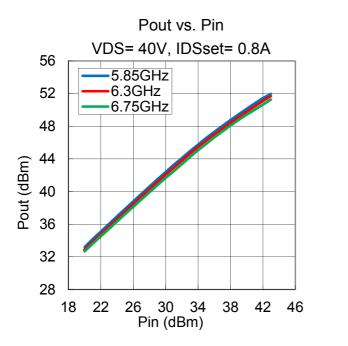
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C

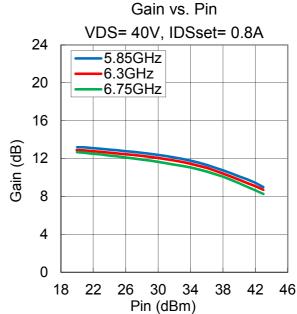
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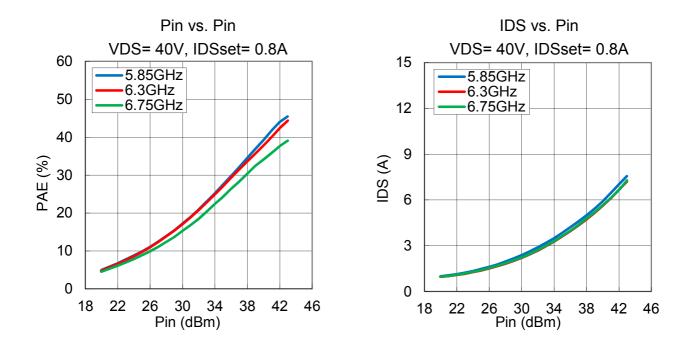
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout, Gain, PAE, IDS vs. Pin

VDS= 40V, IDSset= 0.8A, f= 5.85, 6.3, 6.75GHz, Ta= +25°C







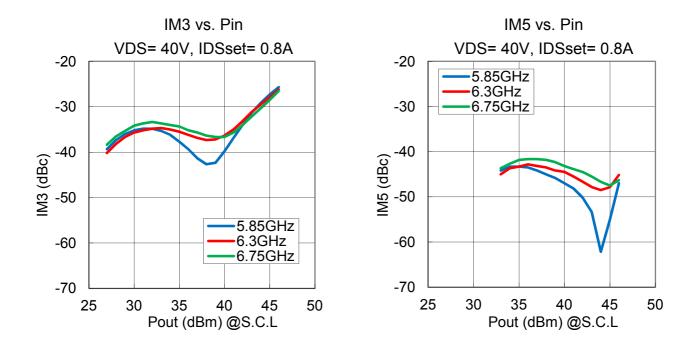
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3, IM5 vs Pout

VDS= 40V, IDSset= 0.8A, f= 5.85, 6.3, 6.75GHz, ∆f= 5MHz, Ta= +25°C

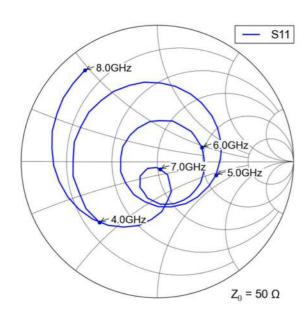


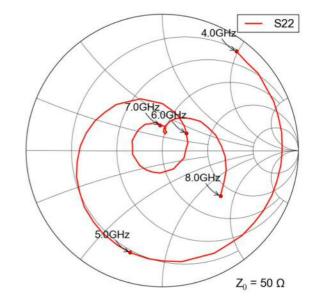
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

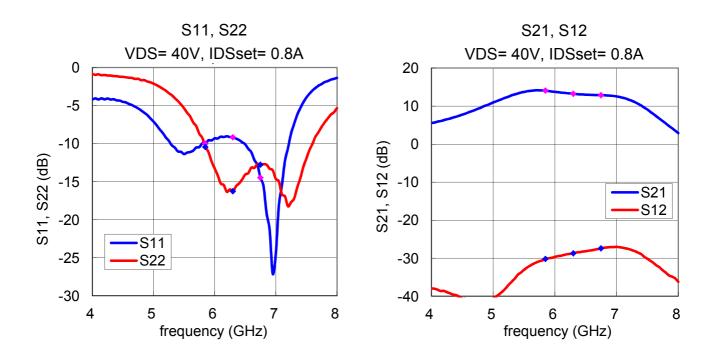
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·S-Parameter

VDS= 40V, IDSset= 0.8A, f= 4 to 8GHz, Ta= +25°C







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MICROWAVE SEMICONDUCTOR TECHNICAL DATA
 4_20190903_No1343 Page: 5 / 6

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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